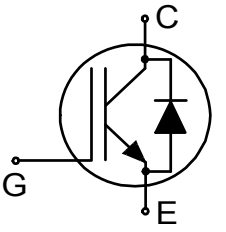
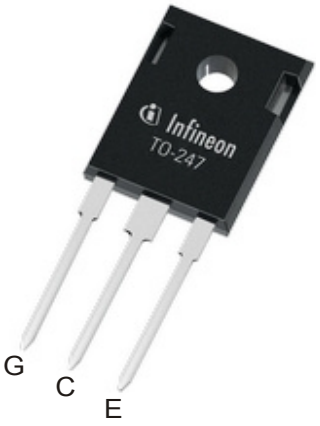
Low Loss DuoPack: IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery antiparallel Emitter Controlled diode

Features:

- Automotive AEC-Q101 qualified
- Designed for DC/AC converters for Automotive Application
- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum junction temperature 175°C
- Dynamically stress tested
- Short circuit withstand time 5µs
- 100% short circuit tested
- 100% of the parts are dynamically tested
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low gate charge Q_G
- Green package
- Very soft, fast recovery antiparallel Emitter Controlled HE diode
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - very high switching speed





Applications:

- Main inverter
- Climate compressor
- PTC heater
- Motor drives

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
AIKW30N60CT	600V	30A	1.5V	175°C	AK30DCT	PG-TO247-3

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Table of Contents

Description 1
Table of Contents 2
Maximum Ratings 3
Thermal Resistance 3
Electrical Characteristics 4
Electrical Characteristics Diagrams 6
Package Drawing 13
Testing Conditions 14
Revision History 15
Disclaimer 16

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 100°C$	I_C	60.0 30.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	90.0	A
Turn off safe operating area $V_{CE} \leq 600V$, $T_{vj} \leq 175°C$, $t_p = 1\mu s$	-	90.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25°C$ value limited by bondwire $T_C = 100°C$	I_F	60.0 30.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	90.0	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time $V_{GE} = 15.0V$, $V_{CC} \leq 400V$ Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s $T_{vj} = 150°C$	t_{SC}	5	µs
Power dissipation $T_C = 25°C$	P_{tot}	187.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature,[1] wave soldering 1.6mm (0.063in.) from case for 10s		260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} Characteristics						
IGBT thermal resistance,[2] junction - case	$R_{th(j-c)}$		-	-	0.80	K/W
Diode thermal resistance,[2] junction - case	$R_{th(j-c)}$		-	-	1.05	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

[1] Package not recommended for surface mount application
[2] Thermal resistance of thermal grease $R_{th(c-s)}$ (case to heat sink) of more than 0.1K/W not included.

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.20mA	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 30.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.50 1.90	2.05 -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 30.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.65 1.60	2.05 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.43mA, V_{CE} = V_{GE}	4.1	4.9	5.7	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 600V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	- -	- 750	40 -	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 30.0A	-	16.7	-	S

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	1630	-	pF
Output capacitance	C_{oes}		-	108	-	
Reverse transfer capacitance	C_{res}		-	50	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 20.0A, V_{GE} = 15V	-	167.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	$I_{C(SC)}$	V_{GE} = 15.0V, V_{CC} ≤ 400V, t_{SC} ≤ 5µs T_{vj} = 150°C	-	275	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 25°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 10.6Ω, $R_{G(off)}$ = 10.6Ω, $L\sigma$ = 136nH, $C\sigma$ = 39pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	23	-	ns
Rise time	t_r		-	21	-	ns
Turn-off delay time	$t_{d(off)}$		-	254	-	ns
Fall time	t_f		-	46	-	ns
Turn-on energy	E_{on}		-	0.69	-	mJ
Turn-off energy	E_{off}		-	0.77	-	mJ
Total switching energy	E_{ts}		-	1.46	-	mJ

Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 30.0A, di_F/dt = 910A/µs	-	85	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.80	-	µC
Diode peak reverse recovery current	I_{rrm}		-	16.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-630	-	A/µs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 175°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 10.6Ω, $R_{G(off)}$ = 10.6Ω, $L\sigma$ = 136nH, $C\sigma$ = 39pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	24	-	ns
Rise time	t_r		-	26	-	ns
Turn-off delay time	$t_{d(off)}$		-	292	-	ns
Fall time	t_f		-	90	-	ns
Turn-on energy	E_{on}		-	1.00	-	mJ
Turn-off energy	E_{off}		-	1.10	-	mJ
Total switching energy	E_{ts}		-	2.10	-	mJ

Diode Characteristic, at T_{vj} = 175°C

Diode reverse recovery time	t_{rr}	T_{vj} = 175°C, V_R = 400V, I_F = 30.0A, di_F/dt = 910A/µs	-	240	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.39	-	µC
Diode peak reverse recovery current	I_{rrm}		-	22.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-320	-	A/µs

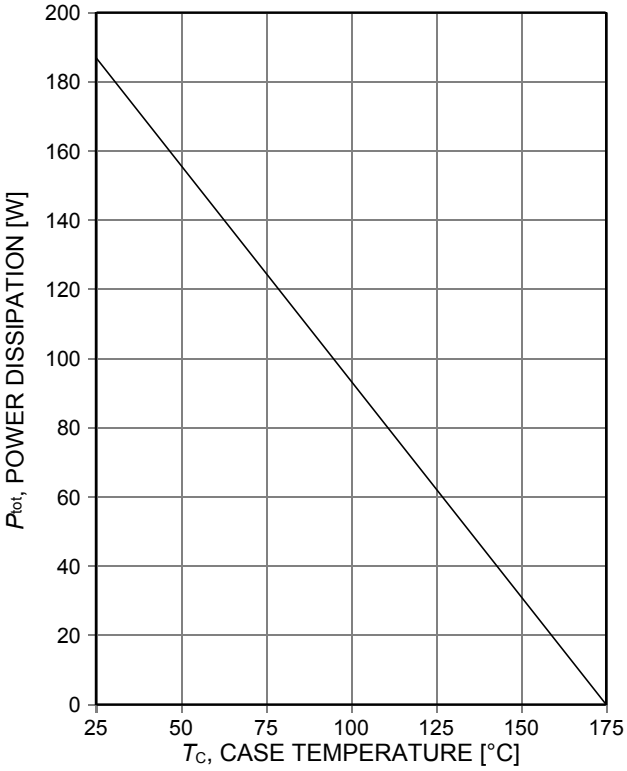


Figure 1. **Power dissipation as a function of case temperature**
(T_j≤175°C)

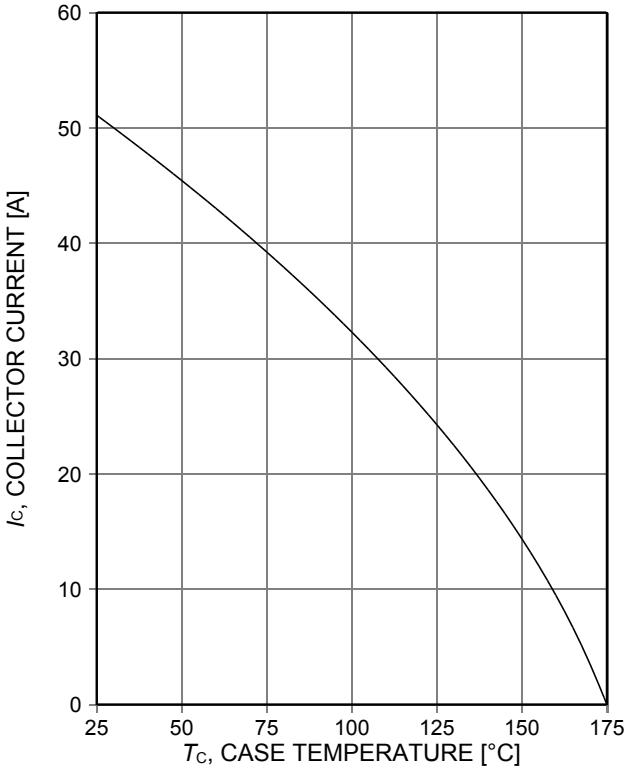


Figure 2. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_j≤175°C)

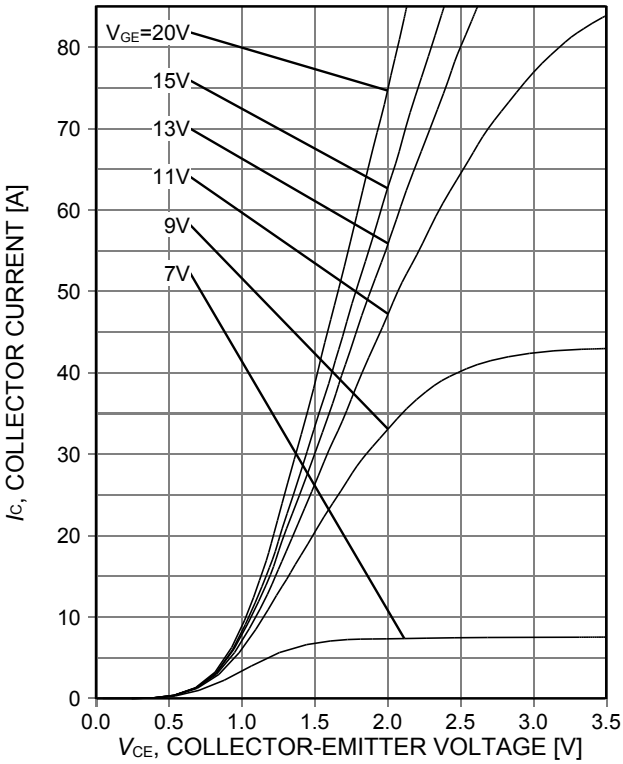


Figure 3. **Typical output characteristic**
(T_j=25°C)

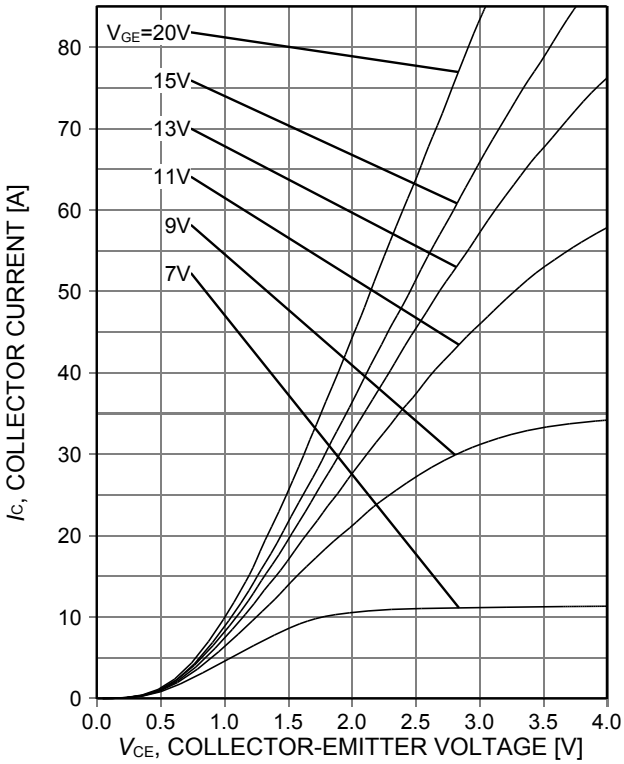


Figure 4. **Typical output characteristic**
(T_j=175°C)

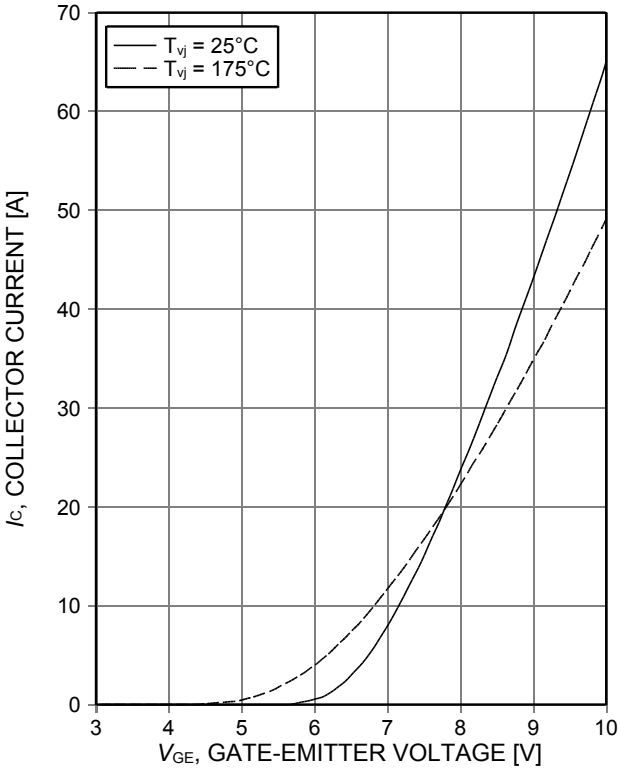


Figure 5. **Typical transfer characteristic** (V_{CE}=20V)

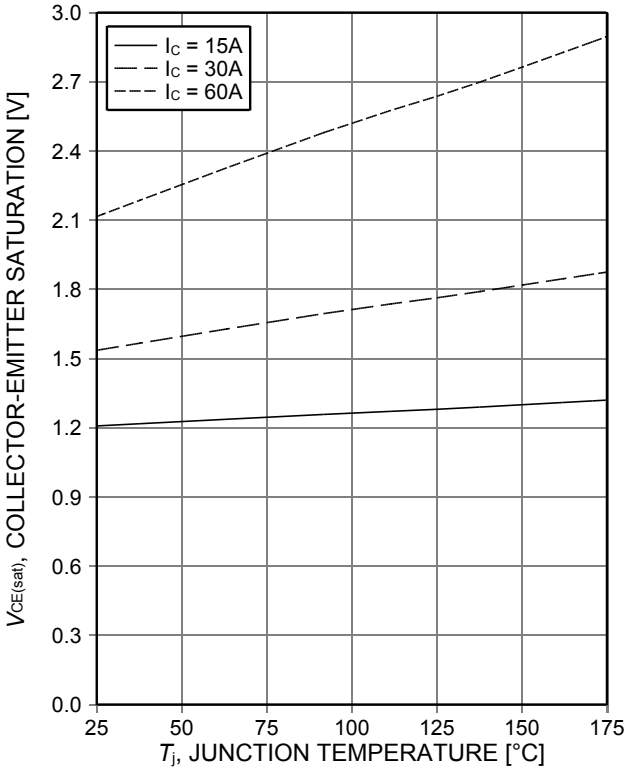


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature** (V_{GE}=15V)

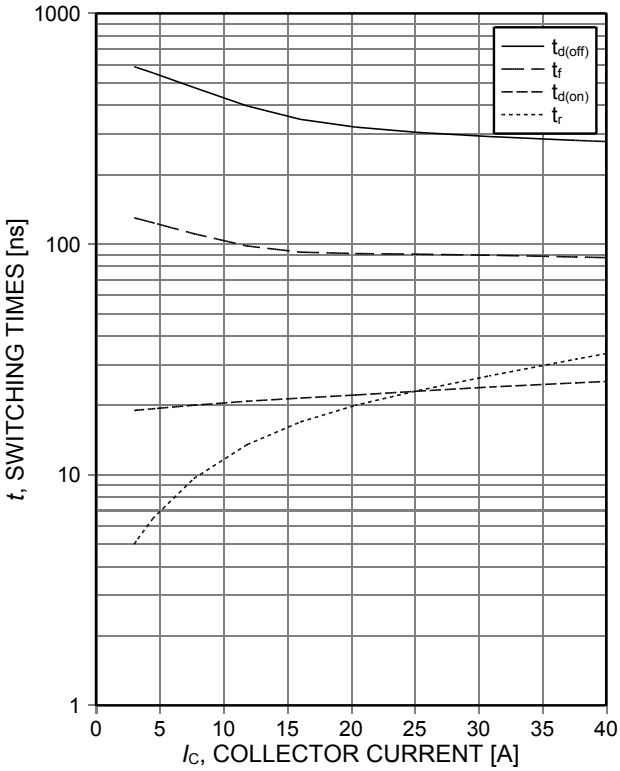


Figure 7. **Typical switching times as a function of collector current** (inductive load, T_j=175°C, V_{CE}=400V, V_{GE}=0/15V, R_G=10Ω, Dynamic test circuit in Figure E)

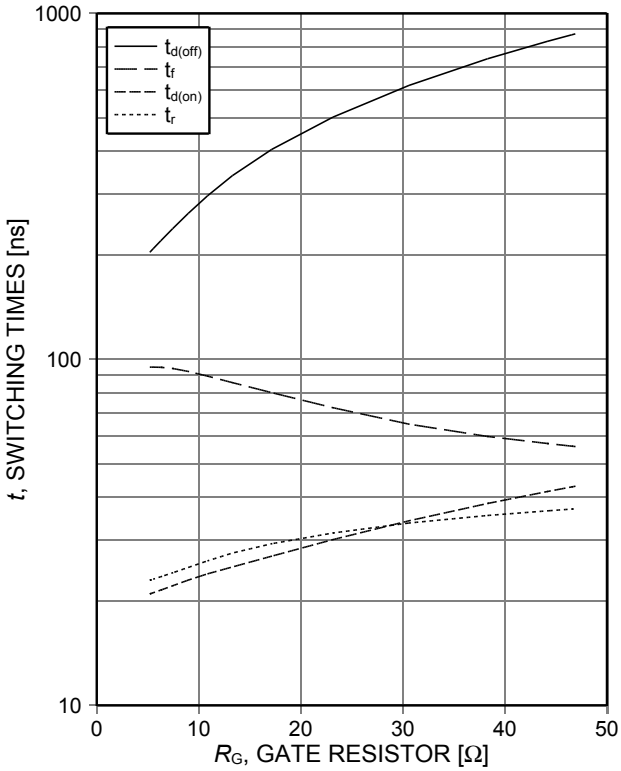


Figure 8. **Typical switching times as a function of gate resistor** (inductive load, T_j=175°C, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, Dynamic test circuit in Figure E)

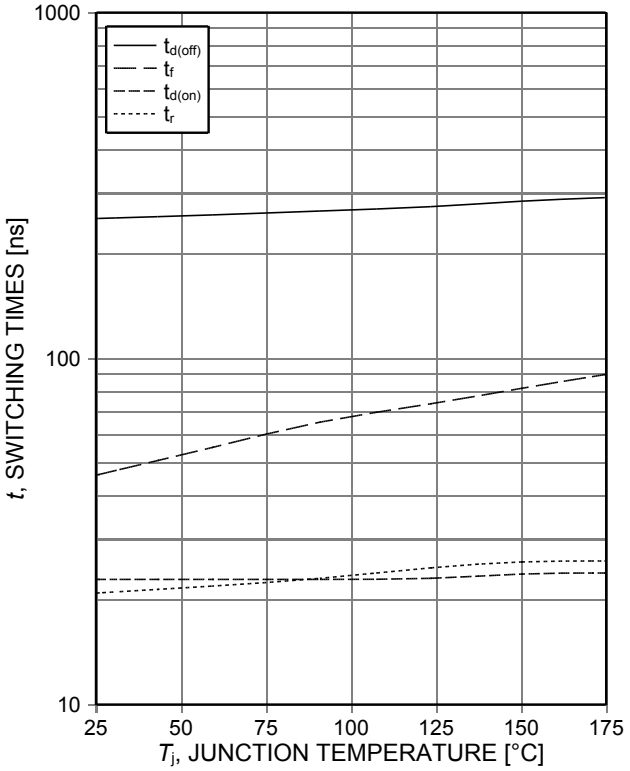


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, R_G=10Ω, Dynamic test circuit in Figure E)

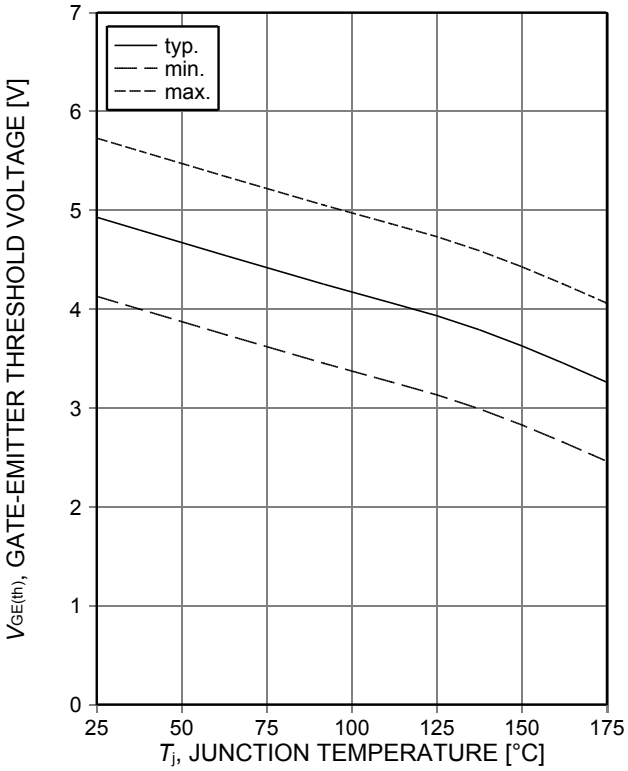


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0,43mA)

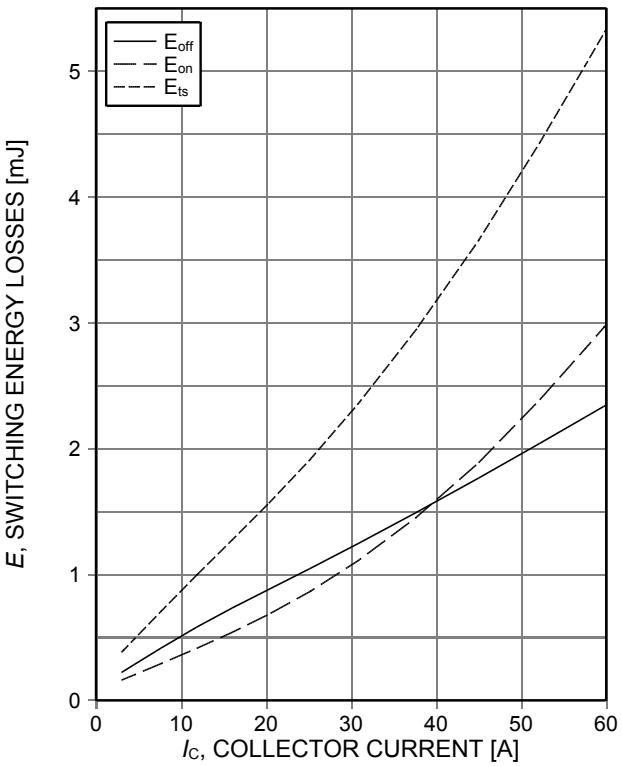


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, T_j=175°C, V_{CE}=400V, V_{GE}=0/15V, R_G=10Ω, Dynamic test circuit in Figure E)

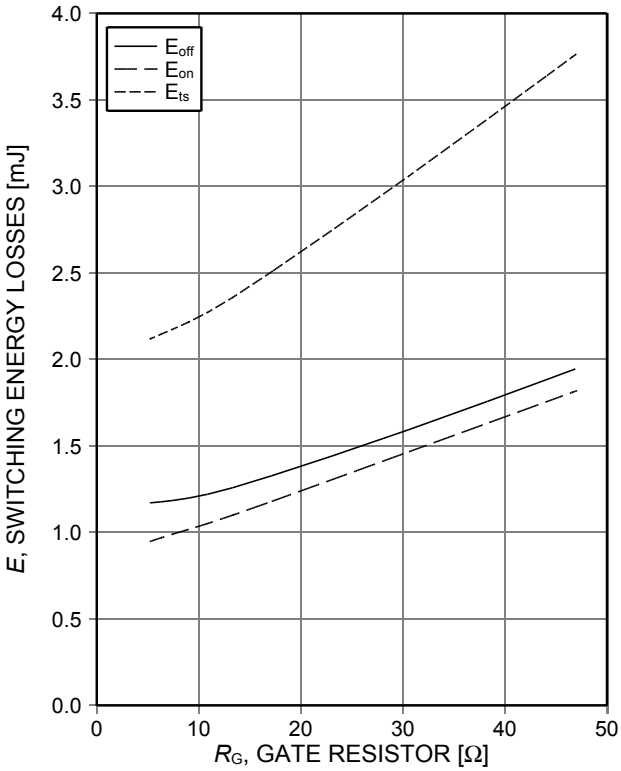


Figure 12. **Typical switching energy losses as a function of gate resistor**
(inductive load, T_j=175°C, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, Dynamic test circuit in Figure E)

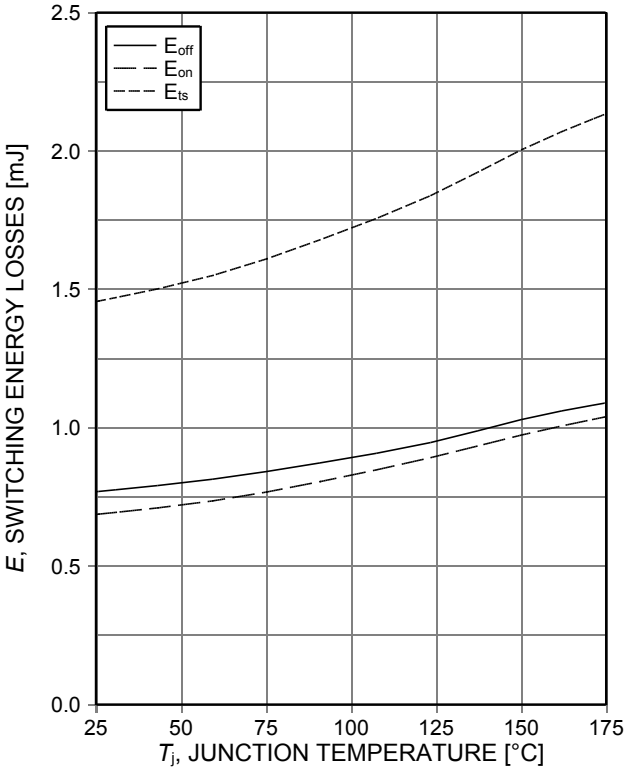


Figure 13. **Typical switching energy losses as a function of junction temperature** (inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, R_G=10Ω, Dynamic test circuit in Figure E)

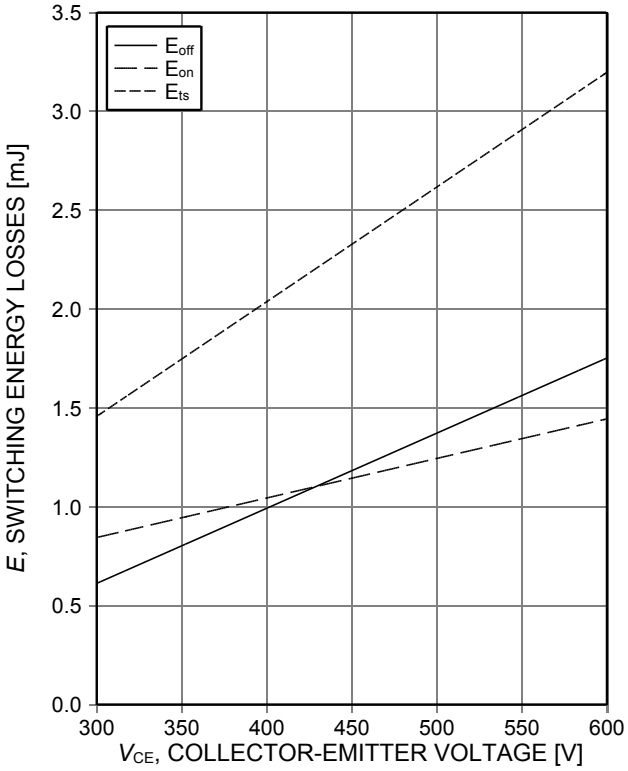


Figure 14. **Typical switching energy losses as a function of collector emitter voltage** (inductive load, T_j=175°C, V_{GE}=0/15V, I_C=30A, R_G=10Ω, Dynamic test circuit in Figure E)

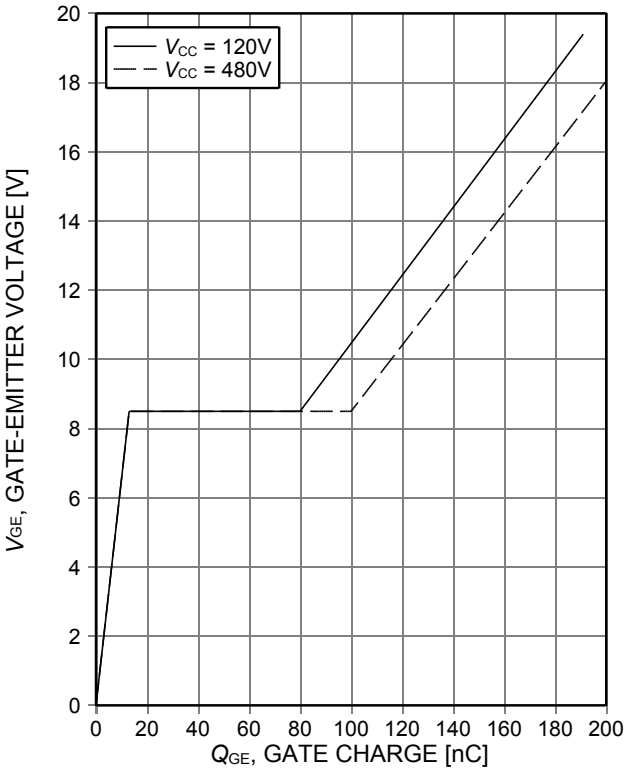


Figure 15. **Typical gate charge** (I_C=30A)

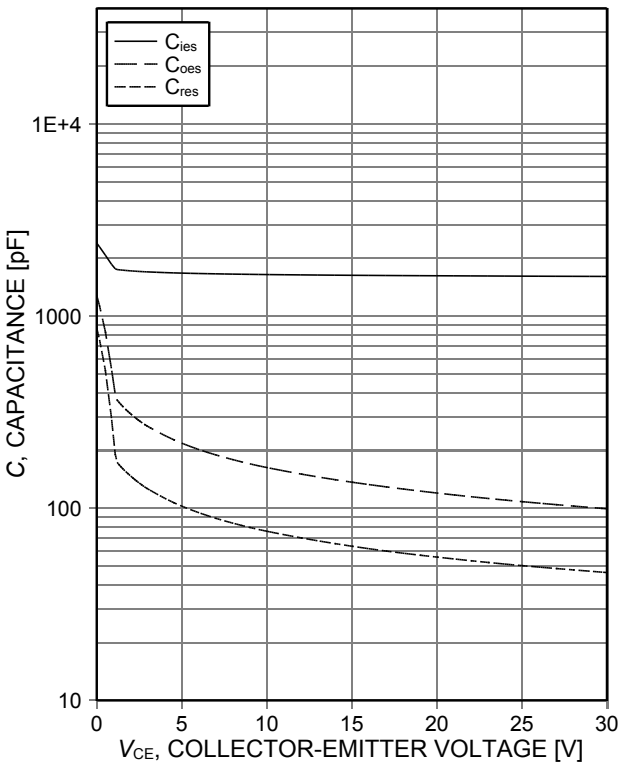


Figure 16. **Typical capacitance as a function of collector-emitter voltage** (V_{GE}=0V, f=1MHz)

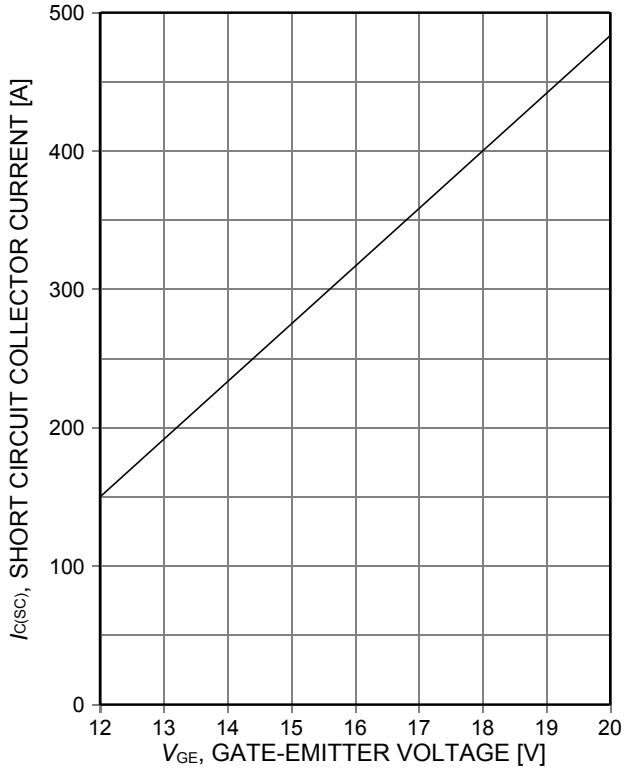


Figure 17. **Typical short circuit collector current as a function of gate-emitter voltage**
(V_{CE}≤400V, start at T_j≤150°C)

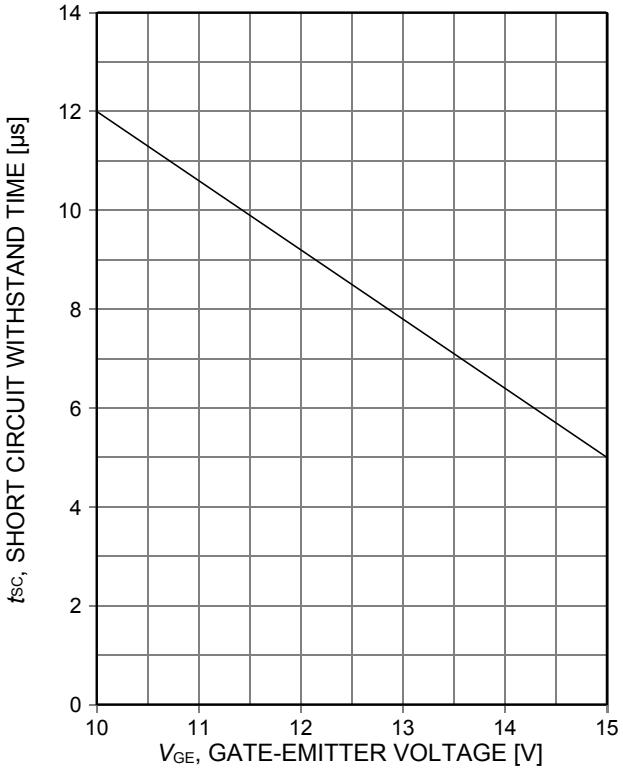


Figure 18. **Short circuit withstand time as a function of gate-emitter voltage**
(V_{CE}=400V, start at T_j=25°C, $T_j$max≤150°C)

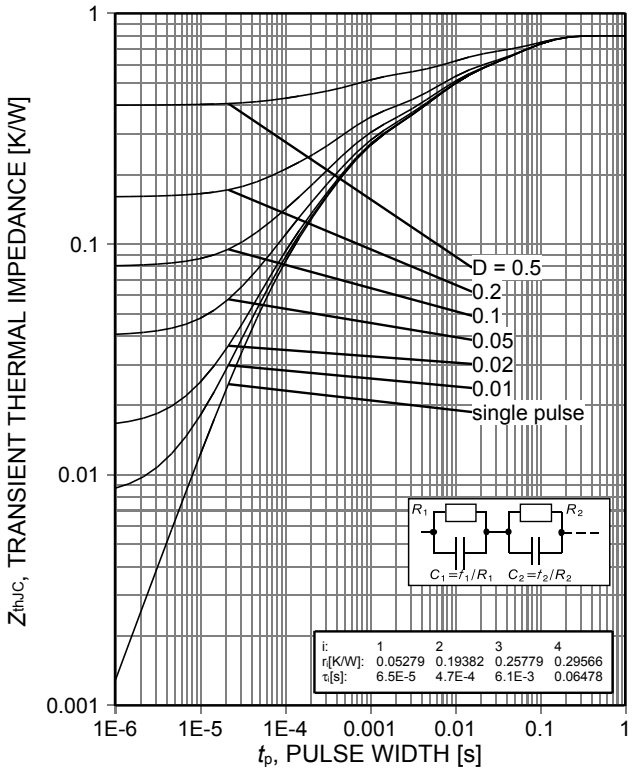


Figure 19. **IGBT transient thermal impedance as a function of pulse width for different duty cycles *D***
(D=t_p/T)

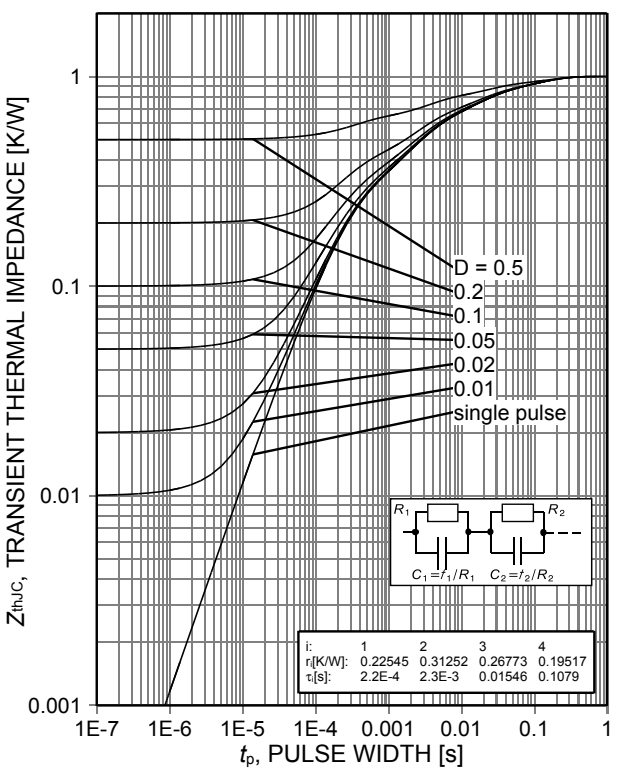


Figure 20. **Diode transient thermal impedance as a function of pulse width for different duty cycles *D***
(D=t_p/T)

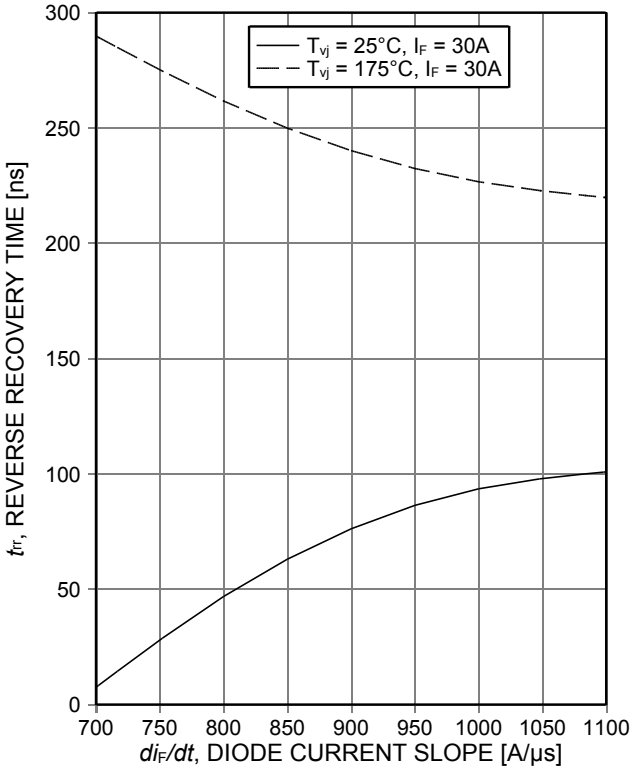


Figure 21. **Typical reverse recovery time as a function of diode current slope**
(V_R=400V,Dynamic test circuit in Figure E)

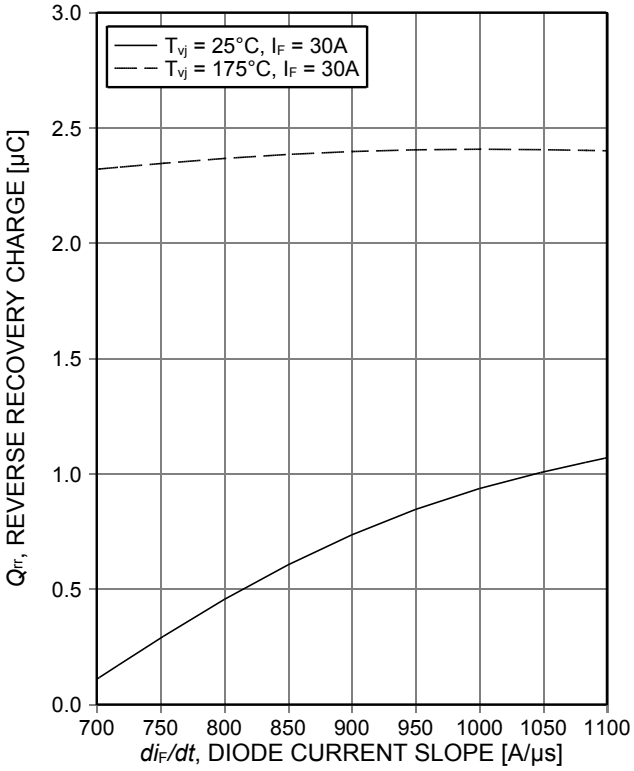


Figure 22. **Typical reverse recovery charge as a function of diode current slope**
(V_R=400V, Dynamic test circuit in Figure E)

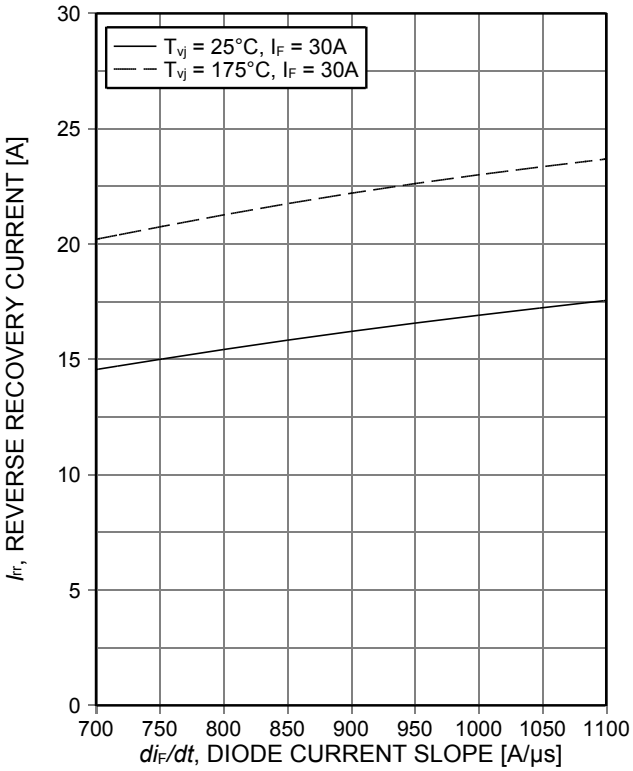


Figure 23. **Typical reverse recovery current as a function of diode current slope**
(V_R=400V, Dynamic test circuit in Figure E)

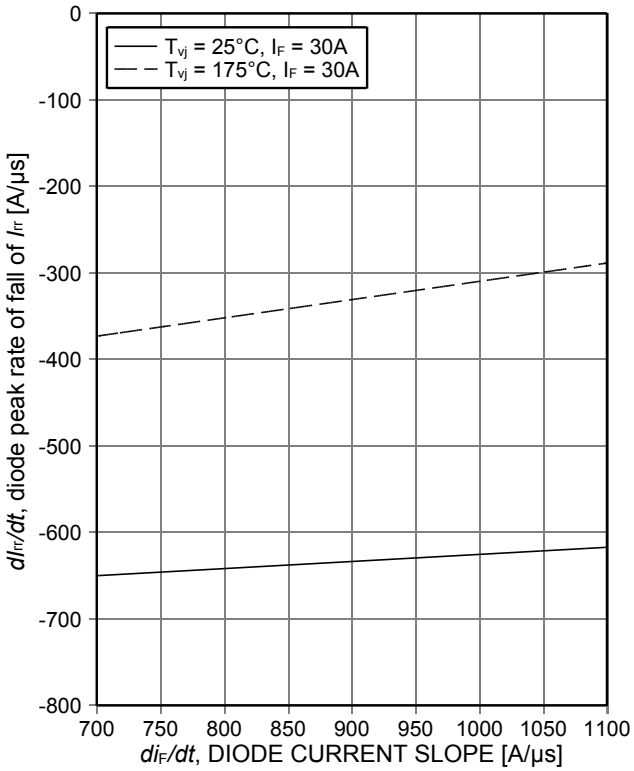


Figure 24. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
(V_R=400V, Dynamic test circuit in Figure E)

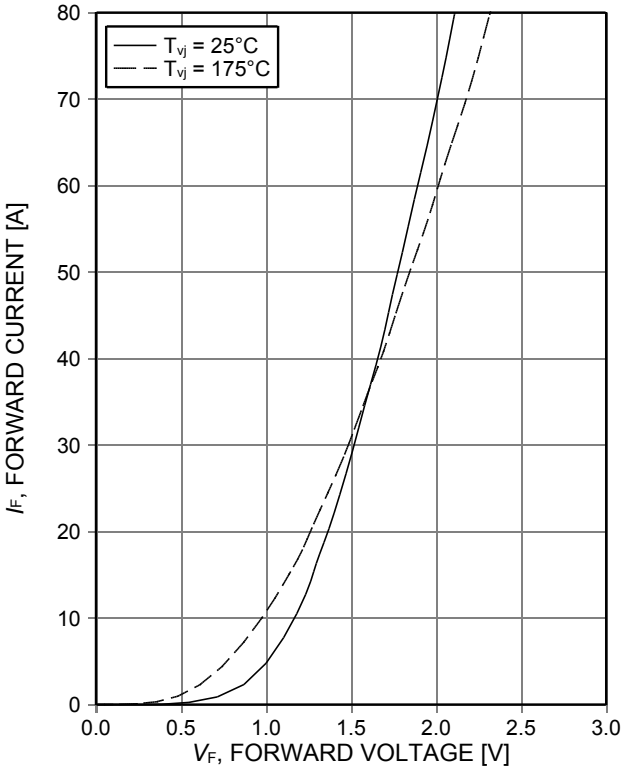


Figure 25. **Typical diode forward current as a function of forward voltage**

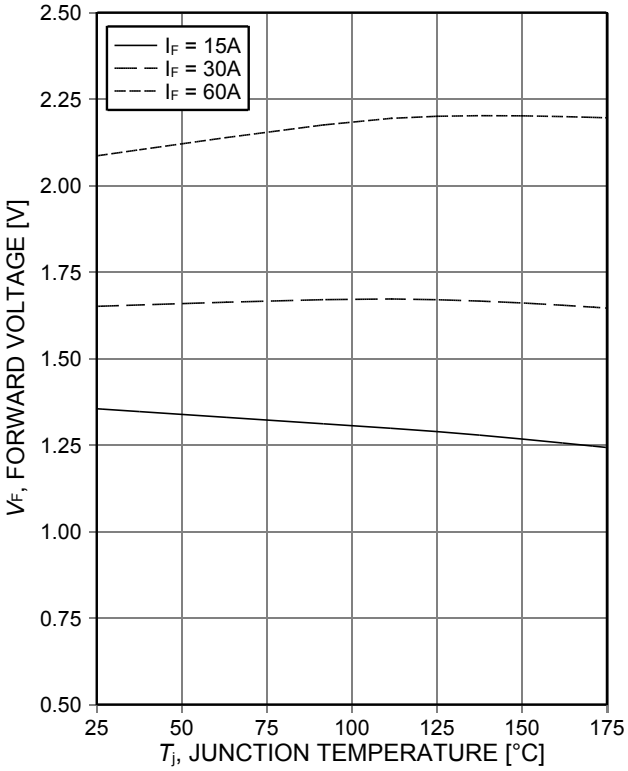
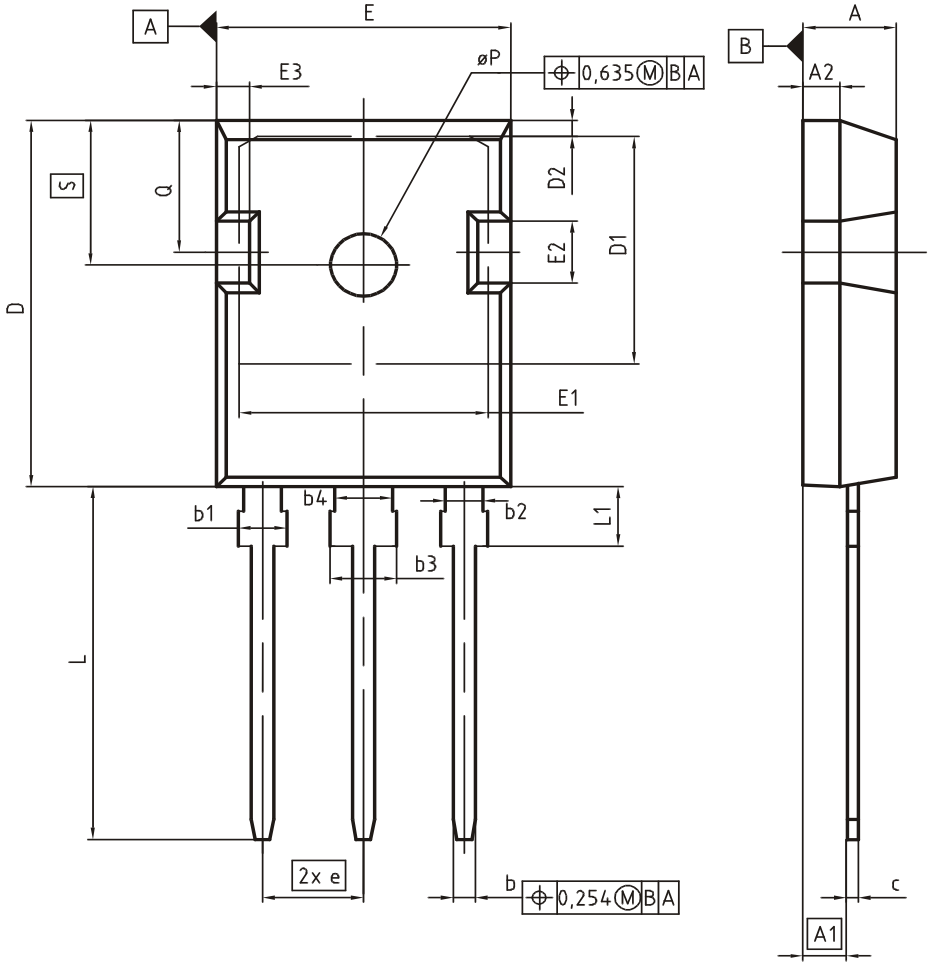


Figure 26. **Typical diode forward voltage as a function of junction temperature**

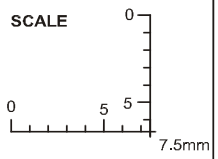
Package Drawing PG-TO247-3



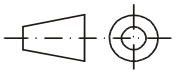
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE



EUROPEAN PROJECTION



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09-07-2010

REVISION
05

Testing Conditions

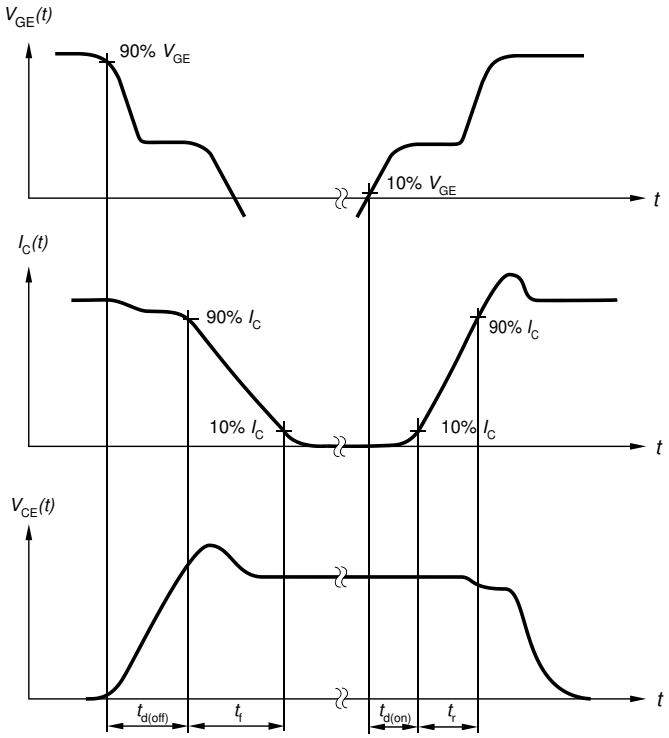

Figure A. **Definition of switching times**

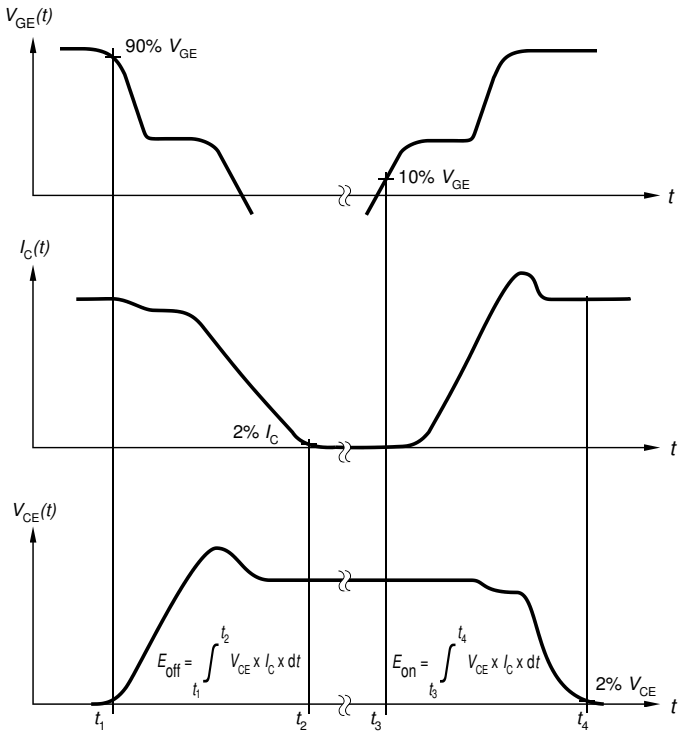

Figure B. **Definition of switching losses**

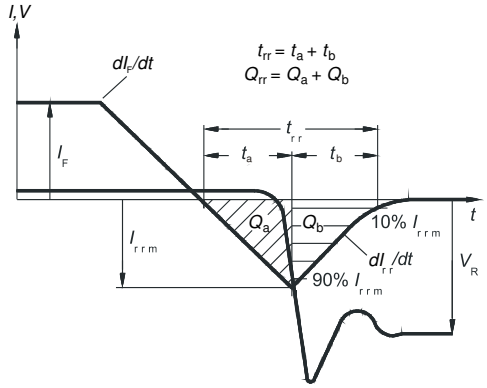

Figure C. **Definition of diode switching characteristics**

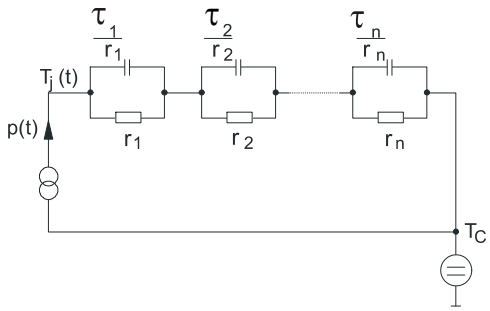

Figure D. **Thermal equivalent circuit**

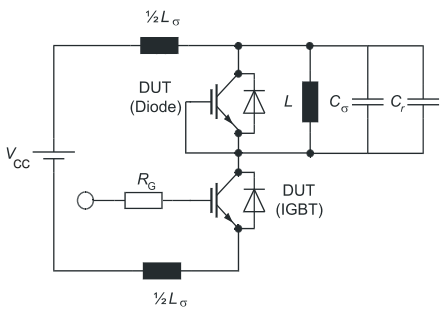

Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

Revision History

AIKW30N60CT

Revision: 2017-02-09, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2017-02-09	Data sheet created

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